

# Maria R Correia

## List of Publications by Year in descending order

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104  
papers

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257101

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3618  
citing authors

#	ARTICLE	IF	CITATIONS
1	Impact of atomic layer deposited TiO <sub>2</sub> on the photocatalytic efficiency of TiO <sub>2</sub> /w-VA-CNT nanocomposite materials. RSC Advances, 2022, 12, 16419-16430.	1.7	2
2	Coupling of plasmonic nanoparticles on a semiconductor substrate <i>via</i> a modified discrete dipole approximation method. Physical Chemistry Chemical Physics, 2022, 24, 19705-19715.	1.3	2
3	Enhancing the luminescence yield of Cr <sup>3+</sup> in <b><math>\hat{I}^2</math></b>-Ga <sub>2</sub> O <sub>3</sub> by proton irradiation. Applied Physics Letters, 2022, 120, .	1.5	8
4	Near band edge and defect emissions in wurtzite Cd <sub>0.025</sub> Mg <sub>0.10</sub> Zn <sub>0.875</sub> O nanocrystals. Optical Materials, 2021, 118, 111227.	1.7	1
5	Exploring swift-heavy ion irradiation of InGaN/GaN multiple quantum wells for green-emitters: the use of Raman and photoluminescence to assess the irradiation effects on the optical and structural properties. Journal of Materials Chemistry C, 2021, 9, 8809-8818.	2.7	5
6	Enhanced optical properties of Cd <sup>2+</sup> -Mg-co-doped ZnO nanoparticles induced by low crystal structure distortion. Journal of Physics and Chemistry of Solids, 2020, 146, 109611.	1.9	11
7	ZnAl <sub>2</sub> O <sub>4</sub> decorated Al-doped ZnO tetrapodal 3D networks: microstructure, Raman and detailed temperature dependent photoluminescence analysis. Nanoscale Advances, 2020, 2, 2114-2126.	2.2	15
8	Electronic Conduction Mechanisms and Defects in Polycrystalline Antimony Selenide. Journal of Physical Chemistry C, 2020, 124, 7677-7682.	1.5	14
9	Identifying Raman modes of Sb <sub>2</sub> Se <sub>3</sub> and their symmetries using angle-resolved polarised Raman spectra. Journal of Materials Chemistry A, 2020, 8, 8337-8344.	5.2	62
10	Probing surface states in C <sub>60</sub> -decorated ZnO microwires: detailed photoluminescence and cathodoluminescence investigations. Nanoscale Advances, 2019, 1, 1516-1526.	2.2	18
11	Eu Activation in $\hat{I}^2$ -Ga <sub>2</sub> O <sub>3</sub> MOVPE Thin Films by Ion Implantation. ECS Journal of Solid State Science and Technology, 2019, 8, Q3097-Q3102.	0.9	15
12	Voids in Kesterites and the Influence of Lamellae Preparation by Focused Ion Beam for Transmission Electron Microscopy Analyses. IEEE Journal of Photovoltaics, 2019, 9, 565-570.	1.5	0
13	Buckminsterfullerene hybridized zinc oxide tetrapods: defects and charge transfer induced optical and electrical response. Nanoscale, 2018, 10, 10050-10062.	2.8	44
14	Optical investigations of europium ion implanted in nitride-based diode structures. Surface and Coatings Technology, 2018, 355, 40-44.	2.2	9
15	Fluctuating potentials in GaAs:Si nanowires: critical reduction of the influence of polytypism on the electronic structure. Nanoscale, 2018, 10, 3697-3708.	2.8	13
16	Multiple optical centers in Eu-implanted AlN nanowires for solid-state lighting applications. Applied Physics Letters, 2018, 113, 201905.	1.5	8
17	Optoelectronic Characterization of ZnO Nanorod Arrays Obtained by Pulse Electrodeposition. Journal of the Electrochemical Society, 2018, 165, D595-D603.	1.3	12
18	Hierarchical Aerographite 3D flexible networks hybridized by InP micro/nanostructures for strain sensor applications. Scientific Reports, 2018, 8, 13880.	1.6	7

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19	On the identification of Sb <sub>2</sub> Se <sub>3</sub> using Raman scattering. MRS Communications, 2018, 8, 865-870.	0.8	73
20	Effect of the Chloride Anions on the Formation of Self-Assembled Diphenylalanine Peptide Nanotubes. IEEE Transactions on Ultrasonics, Ferroelectrics, and Frequency Control, 2018, 65, 1563-1570.	1.7	6
21	Eu-Doped AlGa <sub>N</sub> /Ga <sub>N</sub> Superlattice-Based Diode Structure for Red Lighting: Excitation Mechanisms and Active Sites. ACS Applied Nano Materials, 2018, 1, 3845-3858.	2.4	14
22	XPS analysis of ZnO:Ga films deposited by magnetron sputtering: Substrate bias effect. Applied Surface Science, 2018, 458, 1043-1049.	3.1	42
23	Growth of $\text{Sb}_{2}\text{S}_{3}$ thin films by selenization of RF sputtered binary precursors. Solar Energy Materials and Solar Cells, 2018, 187, 219-226.	3.0	45
24	Hybridization of Zinc Oxide Tetrapods for Selective Gas Sensing Applications. ACS Applied Materials & Interfaces, 2017, 9, 4084-4099.	4.0	135
25	SiGe layer thickness effect on the structural and optical properties of well-organized SiGe/SiO <sub>2</sub> multilayers. Nanotechnology, 2017, 28, 345701.	1.3	5
26	Light-induced nonthermal population of optical phonons in nanocrystals. Physical Review B, 2017, 95, .	1.1	20
27	Multifunctional Materials: A Case Study of the Effects of Metal Doping on ZnO Tetrapods with Bismuth and Tin Oxides. Advanced Functional Materials, 2017, 27, 1604676.	7.8	140
28	Structure and Electrical-Transport Relations in Ba(Zr,Pr)O <sub>3</sub> Perovskites. Inorganic Chemistry, 2017, 56, 9120-9131.	1.9	9
29	Substrate and Mg doping effects in GaAs nanowires. Beilstein Journal of Nanotechnology, 2017, 8, 2126-2138.	1.5	7
30	Correction to "Spectroscopic Analysis of Eu <sup>3+</sup> Implanted and Annealed GaN Layers and Nanowires". Journal of Physical Chemistry C, 2016, 120, 6907-6908.	1.5	5
31	Diamond SAW devices: a reverse fabrication method. Physica Status Solidi C: Current Topics in Solid State Physics, 2016, 13, 53-58.	0.8	3
32	Site Redistribution, Partial Frozen-in Defect Chemistry, and Electrical Properties of Ba <sub>1-x</sub> (Zr,Pr)O <sub>3</sub> . Inorganic Chemistry, 2016, 55, 8552-8563.	1.9	9
33	Electrical insulation properties of RF-sputtered LiPON layers towards electrochemical stability of lithium batteries. Journal Physics D: Applied Physics, 2016, 49, 485301.	1.3	7
34	Analysis of the Tb <sup>3+</sup> recombination in ion implanted Al Ga <sub>1-x</sub> N (0 ≤ x ≤ 1) layers. Journal of Luminescence, 2016, 178, 249-258.	1.5	7
35	Study of damage formation and annealing of implanted III-nitride semiconductors for optoelectronic devices. Nuclear Instruments & Methods in Physics Research B, 2016, 379, 251-254.	0.6	17
36	Quantum well intermixing and radiation effects in InGa <sub>N</sub> /Ga <sub>N</sub> multi quantum wells. , 2016, , .		1

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37	Effect of AlN content on the lattice site location of terbium ions in Al <sub>x</sub> Ga <sub>1-x</sub> N compounds. Semiconductor Science and Technology, 2016, 31, 035026.	1.0	12
38	Luminescence studies on green emitting InGaN/GaN MQWs implanted with nitrogen. Scientific Reports, 2015, 5, 9703.	1.6	19
39	Photoluminescence studies of a perceived white light emission from a monolithic InGaN/GaN quantum well structure. Scientific Reports, 2015, 5, 13739.	1.6	19
40	The Role of Edge Dislocations on the Red Luminescence of ZnO Films Deposited by RF-Sputtering. Journal of Nanomaterials, 2015, 2015, 1-11.	1.5	3
41	Effect of N <sub>2</sub> and H <sub>2</sub> plasma treatments on band edge emission of ZnO microrods. Scientific Reports, 2015, 5, 10783.	1.6	43
42	Spectroscopic Analysis of Eu <sup>3+</sup> Implanted and Annealed GaN Layers and Nanowires. Journal of Physical Chemistry C, 2015, 119, 17954-17964.	1.5	13
43	Structural, optical, electrical and morphological study of transparent p-NiO/n-ZnO heterojunctions grown by PLD. Proceedings of SPIE, 2015, , .	0.8	4
44	Peculiar Magnetoelectric Coupling in BaTiO <sub>3</sub> :Fe <sub>113</sub> Åppm Nanoscopic Segregations. ACS Applied Materials & Interfaces, 2015, 7, 24741-24747.	4.0	9
45	ZnO micro/nanocrystals grown by laser assisted flow deposition. , 2014, , .		1
46	New insights into the temperature-dependent photoluminescence of Mg-doped GaAs nanowires and epilayers. Journal of Materials Chemistry C, 2014, 2, 7104.	2.7	14
47	Impact of composition and morphology on the optical properties of Si-NC/P3HT thin films processed from solution. Applied Physics A: Materials Science and Processing, 2013, 113, 439-446.	1.1	2
48	Influence of RF-sputtering power on formation of vertically stacked Si <sub>1-x</sub> Ge <sub>x</sub> nanocrystals between ultra-thin amorphous Al <sub>2</sub> O <sub>3</sub> layers: structural and photoluminescence properties. Journal Physics D: Applied Physics, 2013, 46, 385301.	1.3	1
49	Resizing of Colloidal Gold Nanorods and Morphological Probing by SERS. Journal of Physical Chemistry C, 2013, 117, 20343-20350.	1.5	13
50	Photoluminescence study of GaAs thin films and nanowires grown on Si(111). Journal of Materials Science, 2013, 48, 1794-1798.	1.7	19
51	Structure and properties of phosphorus-carbide thin solid films. Thin Solid Films, 2013, 548, 247-254.	0.8	17
52	On the origin of strain relaxation in epitaxial CdZnO layers. , 2013, , .		0
53	Structural and optical characterization of Mg-doped GaAs nanowires grown on GaAs and Si substrates. Journal of Applied Physics, 2013, 114, .	1.1	25
54	Disorder induced violet/blue luminescence in rf-deposited ZnO films. Physica Status Solidi C: Current Topics in Solid State Physics, 2013, 10, 662-666.	0.8	13

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55	Effect of oxygen pressure on the structural and magnetic properties of thin Zn <sub>0.98</sub> Mn <sub>0.02</sub> O films. EPJ Applied Physics, 2012, 57, 10301.	0.3	5
56	Large-area high-throughput synthesis of monolayer graphene sheet by Hot Filament Thermal Chemical Vapor Deposition. Scientific Reports, 2012, 2, 682.	1.6	138
57	Facile synthesis of hydrogenated reduced graphene oxide via hydrogen spillover mechanism. Journal of Materials Chemistry, 2012, 22, 10457.	6.7	52
58	Synthesis, structural and optical characterization of ZnO crystals grown in the presence of silver. Thin Solid Films, 2012, 520, 4717-4721.	0.8	14
59	Resonant Raman scattering in ZnO:Mn and ZnO:Mn:Al thin films grown by RF sputtering. Journal of Physics Condensed Matter, 2011, 23, 334205.	0.7	26
60	Al <sub>1-x</sub> In <sub>x</sub> N/GaN bilayers: Structure, morphology, and optical properties. Physica Status Solidi (B): Basic Research, 2010, 247, 1740-1746.	0.7	10
61	Thermal conductance of the AlN/Si and AlN/SiC interfaces calculated with taking into account the detailed phonon spectra of the materials and the interface conditions. Physica Status Solidi C: Current Topics in Solid State Physics, 2010, 7, 60-63.	0.8	0
62	Total reflectance and Raman studies in Al <sub>y</sub> In <sub>x</sub> Ga <sub>1-x-y</sub> N epitaxial layers. Physica Status Solidi C: Current Topics in Solid State Physics, 2010, 7, 56-59.	0.8	0
63	Partial oxidation of methane over bimetallic nickel-lanthanide oxides. Journal of Alloys and Compounds, 2010, 489, 316-323.	2.8	40
64	Partial oxidation of methane over bimetallic copper- and nickel-actinide oxides (Th, U). Journal of Alloys and Compounds, 2010, 497, 249-258.	2.8	24
65	Thermal conductivity of silicon bulk and nanowires: Effects of isotopic composition, phonon confinement, and surface roughness. Journal of Applied Physics, 2010, 107, 083503.	1.1	93
66	Structural and optical properties of Zn <sub>0.9</sub> Mn <sub>0.1</sub> O/ZnO core-shell nanowires designed by pulsed laser deposition. Journal of Applied Physics, 2009, 106, .	1.1	13
67	Directional dependence of AlN intrinsic complex dielectric function, optical phonon lifetimes, and decay channels measured by polarized infrared reflectivity. Journal of Applied Physics, 2009, 106, .	1.1	30
68	Raman scattering on overtones of fully symmetric LO phonons in Zn <sub>0.9</sub> Mn <sub>0.1</sub> O nanocrystals under resonance excitation conditions. Technical Physics Letters, 2009, 35, 1086-1089.	0.2	3
69	Optical and structural properties of ZnO nanorods grown by pulsed laser deposition without a catalyst. Technical Physics, 2009, 54, 1607-1611.	0.2	5
70	Photoluminescence and Raman study of a tensilely strained Si type-II quantum well on a relaxed SiGe graded buffer. IOP Conference Series: Materials Science and Engineering, 2009, 6, 012023.	0.3	1
71	Defect studies on fast and thermal neutron irradiated GaN. Nuclear Instruments & Methods in Physics Research B, 2008, 266, 2780-2783.	0.6	20
72	Hydrothermal synthesis, structural, and spectroscopic studies of vanadium substituted ETS-4. Microporous and Mesoporous Materials, 2008, 110, 436-441.	2.2	16

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73	Electronic properties of Ge islands embedded in multilayer and superlattice structures. <i>Thin Solid Films</i> , 2008, 517, 303-305.	0.8	2
74	Radiation hardness of GeSi heterostructures with thin Ge layers. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2008, 147, 191-194.	1.7	7
75	Role of optical phonon in Ge thermal conductivity. <i>Applied Physics Letters</i> , 2008, 92, 211903.	1.5	22
76	Chemisorption of Phosphoric Acid and Surface Characterization of As Passivated AlN Powder Against Hydrolysis. <i>Langmuir</i> , 2008, 24, 5359-5365.	1.6	27
77	Contribution of the decay of optical phonons into acoustic phonons to the thermal conductivity of AlN. <i>Physical Review B</i> , 2008, 77, .	1.1	23
78	Optical studies of ZnO nanocrystals doped with Eu <sup>3+</sup> ions. <i>Applied Physics A: Materials Science and Processing</i> , 2007, 88, 129-133.	1.1	53
79	Optical active centres in ZnO samples. <i>Journal of Non-Crystalline Solids</i> , 2006, 352, 1453-1456.	1.5	18
80	Investigations of p-type signal for ZnO thin films grown on (100) GaAs substrates by pulsed laser deposition. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2006, 3, 1038-1041.	0.8	16
81	Optical studies on a coherent InGaN/GaN layer. <i>Superlattices and Microstructures</i> , 2006, 40, 452-457.	1.4	2
82	Comment on "Direct evidence of nanocluster-induced luminescence in InGaN epilayers" [Appl. Phys. Lett. 86, 021911 (2005)]. <i>Applied Physics Letters</i> , 2005, 87, 136101.	1.5	3
83	Direct evidence for strain inhomogeneity in In <sub>x</sub> Ga <sub>1-x</sub> N epilayers by Raman spectroscopy. <i>Applied Physics Letters</i> , 2004, 85, 2235-2237.	1.5	21
84	Optical studies on the red luminescence of InGaN epilayers. <i>Superlattices and Microstructures</i> , 2004, 36, 625-632.	1.4	8
85	Annealing behavior and lattice site location of Er implanted InGaN. <i>Nuclear Instruments &amp; Methods in Physics Research B</i> , 2003, 206, 1042-1046.	0.6	3
86	Phonons and free-carrier properties of binary, ternary, and quaternary group-III nitride layers measured by Infrared Spectroscopic Ellipsometry. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2003, 0, 1750-1769.	0.8	16
87	Degradation of Structural and Optical Properties of InGaN/GaN Multiple Quantum Wells with Increasing Number of Wells. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2003, 0, 302-306.	0.8	4
88	Analysis of Strain Depth Variations in an In <sub>0.19</sub> Ga <sub>0.81</sub> N Layer by Raman Spectroscopy. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2003, 0, 563-567.	0.8	7
89	Raman study of the A <sub>1</sub> (LO) phonon in relaxed and pseudomorphic InGaN epilayers. <i>Applied Physics Letters</i> , 2003, 83, 4761-4763.	1.5	53
90	Structural and optical properties of InGaN/GaN layers close to the critical layer thickness. <i>Applied Physics Letters</i> , 2002, 81, 1207-1209.	1.5	94

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91	Strain and composition distributions in wurtzite InGaN/GaN layers extracted from x-ray reciprocal space mapping. Applied Physics Letters, 2002, 80, 3913-3915.	1.5	209
92	Preliminary investigations of infrared Er-related photoluminescence in ion-implanted In <sub>0.07</sub> Ga <sub>0.93</sub> N. Applied Physics Letters, 2002, 80, 4504-4506.	1.5	6
93	Strain relaxation and compositional analysis of InGaN/GaN layers by Rutherford backscattering. Nuclear Instruments & Methods in Physics Research B, 2002, 190, 560-564.	0.6	10
94	Splitting of X-ray diffraction and photoluminescence peaks in InGaN/GaN layers. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2002, 93, 163-167.	1.7	20
95	Interpretation of double x-ray diffraction peaks from InGaN layers. Applied Physics Letters, 2001, 79, 1432-1434.	1.5	55
96	Depth Resolved Studies of Indium Content and Strain in InGaN Layers. Physica Status Solidi (B): Basic Research, 2001, 228, 59-64.	0.7	7
97	Indium content determination related with structural and optical properties of InGaN layers. Journal of Crystal Growth, 2001, 230, 448-453.	0.7	8
98	Green, red and infrared Er-related emission in implanted GaN:Er and GaN:Er,O samples. Journal of Applied Physics, 2001, 89, 6183-6188.	1.1	34
99	Compositional pulling effects in In <sub>x</sub> Ga <sub>1-x</sub> N/GaN layers: a combined depth-resolved cathodoluminescence and Rutherford backscattering/channeling study. Physical Review B, 2001, 64, .	1.1	176
100	Compositional dependence of the strain-free optical band gap in In <sub>x</sub> Ga <sub>1-x</sub> N layers. Applied Physics Letters, 2001, 78, 2137-2139.	1.5	104
101	Strain and Compositional Analysis of InGaN/GaN Layers. Materials Research Society Symposia Proceedings, 2000, 639, 3521.	0.1	3
102	Raman spectroscopy studies in InGaN/GaN wurtzite epitaxial films. Materials Research Society Symposia Proceedings, 2000, 639, 6101.	0.1	2
103	Steady-state and time-resolved luminescence in InGaN layers. Journal of Luminescence, 2000, 87-89, 1202-1205.	1.5	1
104	Distribution of 1.68 eV emission from diamond films. Journal of Applied Physics, 1998, 84, 2207-2211.	1.1	5